

Nanogranular MgB₂ thin films on SiC buffered Si substrates prepared by in-situ method

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MgB₂ thin films were deposited on SiC buffered Si substrates by sequential electron beam evaporation of B-Mg bilayer followed by in-situ annealing. The application of a SiC buffer layer enables the maximum annealing temperature of 830°C. The Transmission Electron Microscopy analysis confirms the growth of a nanogranular MgB₂ film and the presence of a Mg₂Si compound at the surface of the film. The 150-200 nm thick films show a maximum zero resistance critical temperature T_{C0} above 37 K and a critical current density J_C ~ 10⁶ A/cm² at 11 K.

1 Introduction

Recently we have used NbN buffered Si(100) substrates for the preparation of the MgB₂ films grown by sequential evaporation of B and Mg with improved superconducting and transport properties [1]. In spite of this fact, the existence of a superconducting NbN buffer layer (T_C ~ 10 K) is not always convenient for some applications. This is a challenge to look for another non-superconducting type of buffer layer on top of the “technological” Si substrate. The potential buffer layer can be chosen on the base of substrates which recently were successfully used for the preparation of MgB₂ films as sapphire [2,3], MgO [4,5], SrTiO₃ [6,7], SiC [8], and SiN [9]. Most of these substrates are monocrystals, often rather expensive (SiC, SrTiO₃). So far, the best results have been obtained by Zeng et al. [8] where high quality MgB₂ films were prepared using a hybrid physical-chemical vapor deposition (HPCVD) technique on top of a monocrystalline 6H-SiC substrate. To the best of our knowledge, no publication reports on the deposition of MgB₂ on SiC buffered Si substrate. This is a reason why we decided to apply an amorphous SiC as buffer layer on top of a Si substrate beside the fact that SiC is an interesting doping material for the powder in tube processed MgB₂ tapes.

The scope of this article is the preparation and the study of some structural and electrical properties of MgB₂ films on SiC buffered Si substrates.

2 Sample preparation

Amorphous silicon carbide buffer layers were grown by plasma enhanced chemical vapor deposition (PE CVD) technique described in [10]. All films were prepared on weakly doped n-type Si substrates Si(100) and Si(111) (resistivity 2-7Ωcm). Prior to the deposition, a

standard cleaning was performed to remove impurities from the silicon surface, and 5% hydrofluoric acid was used to remove the native oxide from the wafer surface. The wafer was then rinsed in deionized water and dried in a nitrogen ambient. The films were deposited in a high frequency parallel-plate plasma reactor in which the frequency, the RF power, and the substrate temperature were maintained at 13.56 MHz, 0.06 Wcm⁻², and 350°C, respectively. Samples with different amounts of N were achieved by small addition of ammonia (NH₃) into the gas mixture of silane SiH₄ and methane CH₄ which were directly introduced into the reaction chamber [10].

MgB₂ films were prepared similarly to [1] by sequential electron beam evaporation of the Mg-B bilayer followed by in-situ annealing. The magnesium and boron layers were deposited on the SiC buffered Si substrates at room temperature. The deposition chamber was evacuated to a pressure of 10⁻⁴ Pa. An excess of about 100% of Mg compared to the stoichiometric composition has been used. The amount of boron corresponds to 200 nm of a stoichiometric MgB₂ film. As-deposited films were in-situ heated to 280°C for 30 min in an argon atmosphere at a pressure of 0.06 Pa. Subsequently, the pressure of Ar was increased up to 16 Pa and the temperature of the heater was increased to the maximum temperature of 830°C and kept there for 10 min. Finally, the Ar pressure was raised to 10³ Pa and the samples were cooled down to room temperature.

3. Characterization an discussion

The final MgB₂ films obtained on the SiC/Si substrate were 150-200 nm thick and often completely or partially covered by the remainder of the unreacted Mg. X-ray diffraction patterns were taken by using a Bragg-Brentano diffractometer. No peaks belonging to the MgB₂ nor to the SiC phase could be detected in any of the samples. This result implies a nanogranular character of the prepared films. This fact is confirmed by Transmission Electron Microscopy (TEM) (JEOL1200EX). The microstructure and the Selected Area Diffraction (SAD) patterns were examined at the surface of the film, at the center of the film and close to the interface with the SiC buffer layer. A conventional Ar ion milling process was used to etch the MgB₂ film. SAD pattern taken at the surface of the film (Fig. 1a) reveals the presence of Mg₂Si besides diffraction rings originating from the MgB₂ hexagonal phase.

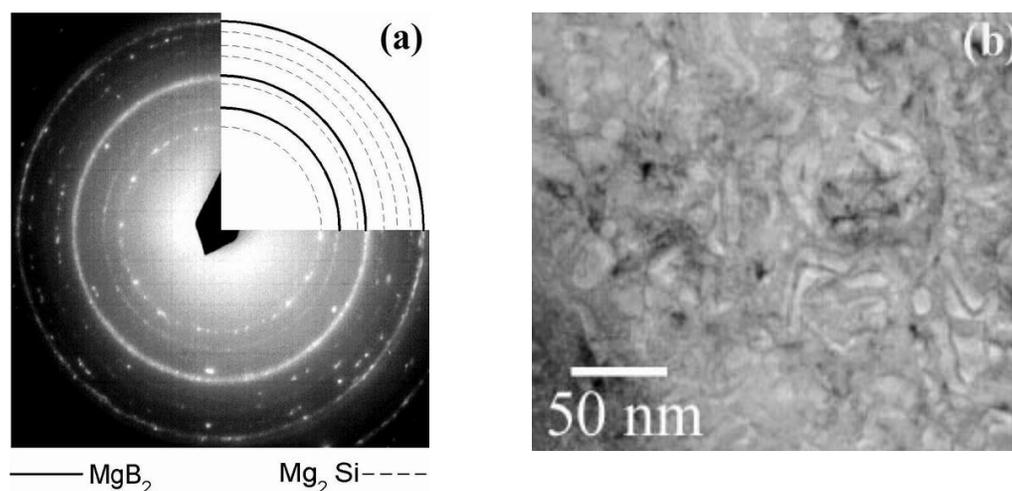


Fig. 1. SAD pattern (a) and the microstructure (b) of the MgB₂ film surface.

A TEM micrograph (Fig.1b) depicts the presence of the Mg_2Si grains with a size of about $10 \times 40 nm^2$. However, SAD pattern taken from the center of the film (Fig.2a) and from the region near the interface with the buffer layer shows diffraction rings belonging to the MgB_2 , only. After the final etching, only amorphous SiC is detected near the interface (Fig.2b).

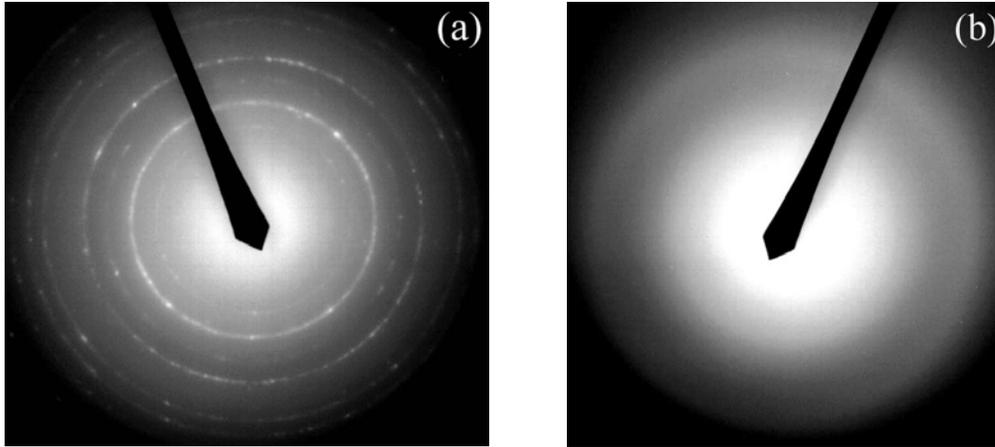


Fig.2. SAD patterns taken from the middle of the MgB_2 film (a) and near the MgB/SiC interface after the final etching (b).

The MgB_2 films on the SiC/Si substrates were investigated by Rutherford backscattering spectrometry (RBS). The experiments were performed with 1.7 MeV He^{++} ions at a scattering angle of 168° . A RBS random spectrum similar to those obtained by Zeng et al. [8] is shown in Fig.3. The experimental points above the channel number 800 unrelated to the sample composition are a consequence of Ag paste used to fix the sample to the holder. Probably due to the instability of the beam for few seconds, this hit the edge of the film.

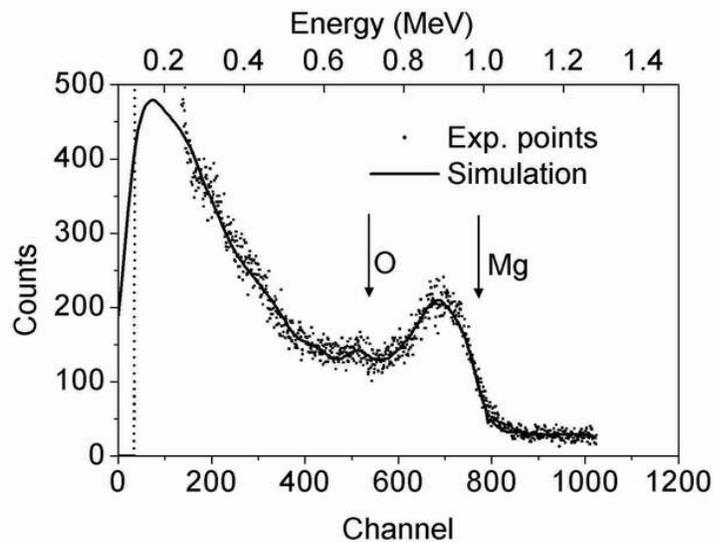


Fig.3. RBS spectrum of a MgB_2 film grown on a SiC/Si substrate

It is possible to correlate a simulated Mg depth profile with the spectrum; however, the simulation of depth profiles for B, C, and Si is difficult because the scattering signals of these elements are superimposed. The simulation of the experimental RBS spectrum shows the presence of oxygen at the surface of the MgB₂ film, which is a hint for a possible presence of MgO as a consequence of the oxidation of the residual Mg or MgB₂ surface.

The superconducting and the transport properties of the MgB₂ films were characterized by resistance measurements using the standard DC four-point method and by measuring of the AC susceptibility. The maximum zero resistance critical temperature T_{C0} was 37.4 K (Fig.4a) and the critical transport current density J_C reached about 10⁶ A/cm² at a temperature of 11 K. In Fig.4b the susceptibility measurements of this sample are shown. The diamagnetic onset was observed at a temperature of T = 37.2 K in the real part (χ') of the susceptibility and is corresponding well to T_{C0}. The width of the diamagnetic transition (10-90%) is 1.2 K, indicating a homogeneous MgB₂ superconducting phase. The imaginary part (χ'') characterizes the midpoint of the diamagnetic transition (T = 36 K) and the AC losses due to this transition. The AC susceptibility measurements were made at a field amplitude of H₀ = 200 A/m.

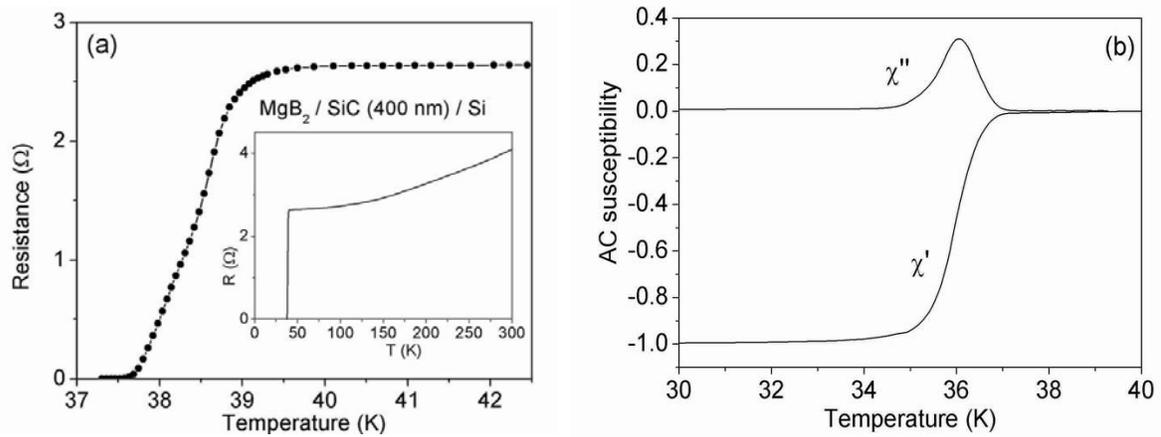


Fig.4. The dependence of the resistance on the temperature of a MgB₂ film (a). The susceptibility measurements of the same film (b).

The philosophy of our MgB₂ growth is based on the fact that the boron film is completely covered by Mg in the as deposited bilayer. We expect an increased pressure of Mg at the B-Mg interface during in-situ annealing and, therefore, an increase of the temperature up to 800 - 900°C is necessary. This temperature range corresponds to a “window” in the P_{Mg}-T phase diagram for MgB₂+Mg-gas, in which MgB₂ does not decompose and an excess of Mg does not condense at the MgB₂ surface [11, 12].

The amorphous SiC layer works as a diffusion barrier between the Si substrate and the MgB₂. We can expect two processes having a negative influence on the critical temperature of the final MgB₂ films.

First, the high temperature of the substrate (above 800°C) during the annealing leads to a degradation of the SiC diffusion barrier. This effect is shown in Fig.5. Fig.5a presents the R-T dependence of the MgB₂ film prepared on top of the SiC/Si substrate (100 nm thick SiC layer) annealed at a temperature of 840°C for 30min prior to the preparation of the MgB₂ film. Fig.5b depicts a much improved R-T dependence of the MgB₂ film prepared by the same process as in the case of the not pre-annealed substrate. We found the optimal thickness of the

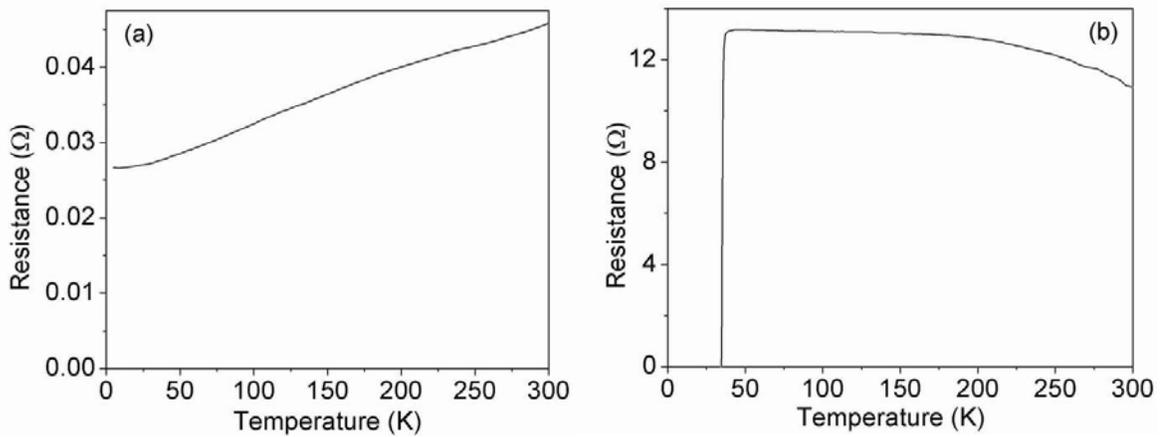


Fig. 5. The dependence of the resistance on the temperature of MgB_2 films prepared on top of a pre-annealed (a) and on an as-deposited (b) 100 nm thick SiC buffer layer.

SiC layer to be ~ 400 nm when even the pre-annealed substrate has no impact at least on T_{C0} of the MgB_2 film.

Secondly, we suppose an interaction (reaction) at the interface between the MgB_2 and the SiC layer, too.

He et al. [13] reported a reaction between MgB_2 and SiC when SiC is mixed with elemental Mg and B in a pressed pellet and annealed at $800^\circ C$ in a sealed Ta tube. SiC suppressed T_C in that case.

Matsumoto et al. [14] studied the effect of SiC doping of the powder on tube processed MgB_2 tapes (SiC doping with a grain size of 30 nm, doping content 1 to 20%). Their results indicated that the doped SiC reacted with Mg forming Mg_2Si at $600^\circ C$. The T_C of SiC doped tape is lowered by 3 K compared with the non-doped tape. However, the J_c values of the in-situ processed tapes were much improved by SiC doping.

Zeng et al. in their HPCVD process exposed a single-crystalline SiC substrate to Mg vapor at $720-760^\circ C$ before B_2H_6 was introduced. On the base of the thermodynamic calculation and the thermodynamic P_{Mg} -T phase diagram of the SiC-Mg system [8], it was shown that no chemical reaction occurs when the Mg partial pressure is about or below 95% of its vapor pressure at the corresponding temperature in the phase diagram.

In our case (see above), Mg_2Si was observed by a TEM analysis at the surface of the MgB_2 film. The formation of Mg_2Si is possible, if it is assumed that Si or SiC diffuse through the whole film up to the surface. However, no Mg_2Si was observed in the bulk of the film. This can be explained if it is assumed that during annealing, the partial pressure of Mg at the B-Mg interface is sufficient for the formation of Mg_2Si ($>95\%$ of the vapor pressure at the corresponding temperature in the phase diagram in [8]). In contrast, the partial pressure of Mg decreases in direction to the bulk of the boron film and film-buffer layer interface, hence, no reaction of Mg with SiC is observed (we suppose the diffusion of Mg into the boron film and the volatility of Mg can assist to automatic composition adjustment as a result of the self-limiting adsorption of Mg [8]). We must admit that the RBS analysis was not able to determine the distribution of C and Si in the film. A further analysis was necessary. We characterized our structure by Heavy Ion Elastic Recoil Detection Analysis (ERDA) [15,16]. The ERDA measurements were performed at the Ion Beam Laboratory of the Hahn-Meitner-

Institut using a beam of 350 MeV Au ions. Fig.6 shows the concentration profiles of the $\text{MgB}_2/\text{SiC}/\text{Si}$ structure in the case when no excess metallic Mg is present at the smooth surface (RMS = 9.41nm for $10 \mu\text{m}^2$ area) of the final uniform MgB_2 film.

The concentration profiles confirm clearly that Mg and B are not a bilayer anymore and they are diffused into each other. Beside this, mixing of SiC with the MgB_2 film and with the Si substrate is evident. These facts support our above suggested assumptions. The presence of oxygen not only at the surface of the film can be linked with amorphous compounds (MgO ?) containing oxygen.

Hydrogen and nitrogen in the film are probably a consequence of the addition of NH_3 during the preparation of the SiC films.

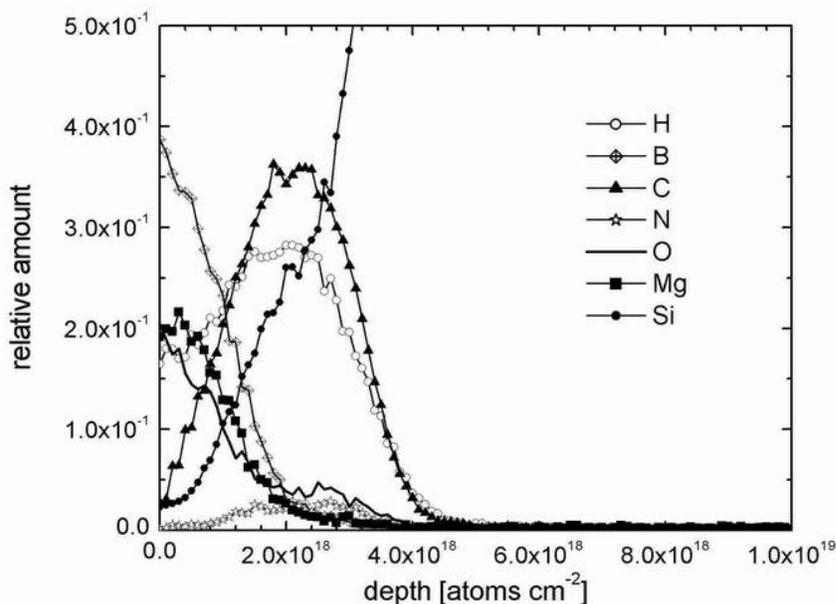


Fig.6. Concentration profiles of the $\text{MgB}_2/\text{SiC}/\text{Si}$ structure obtained by ERDA.

4. Conclusion

In this paper we have reported on the preparation of the MgB_2 thin films by sequential deposition using in-situ annealing on SiC buffered Si substrates. The maximum zero resistance critical temperature $T_{C0} = 37.4$ K is higher than the previously reported values for the MgB_2 films on Si substrates, while the critical current density J_C is comparable with that of polycrystalline films. The presence of the SiC buffer layer enables an high annealing temperature of 830°C , necessary for the growth process. The TEM analysis revealed the presence of Mg_2Si at the surface of the film, while the bulk of the film is free of this compound, at least in the crystalline form. ERDA confirms the diffusion of SiC into the MgB_2 film.

5. Acknowledgement

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6. References

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